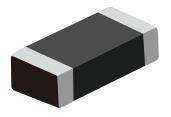


FEATURES

Fast response, instantly clamping the transient over voltage. High surge current handling capability. High energy absorption capability. Low clamping voltages, providing better surge protection. Low capacitance values, providing digital switching circuitry protection. High insulation resistance, preventing electric arcing to the adjacent devices or circuits.



APPLICATIONS

Universal Serial Bus (USB).	
Mobile communication.	
Computer/DSP product.	
Video and audio ports.	
Portable/Hand-Held Products.	
Data, Diagnostic I/O ports.	

APPROVALS

R	oHS	Compliance with 2011/65/EU
Н	F	Compliance with IEC61249-2-21:2003

ELECTRICAL SPECIFICATION

Test condition		
Varistor voltage	In = 1 mA DC	
Leakage current	Vdc = 5 V DC	
Maximum clamping voltage	Ic = 1 A	
Rated peak single pulse transient current	8 / 20 µs waveform, +/- each 1 time induce	
Capacitance	10/1000 μs waveform	
Insulation resistance after reflow soldering	f = 1MHz, Vrms = 0.5 V	



ELECTRICAL SPECIFICATION

Electrical specification				
Maximum allowable continuous DC voltage	5	V		
trigger voltage / Varistor voltage / breakdown voltage	125	V		
Maximum clamping voltage	220	V	Maximum	
Rated peak single pulse transient current	1	А	Maximum	
Nonlinearity coefficient	> 12			
Leakage current at continuous DC voltage	< 0.1	uA		
Response time	< 0.5	ns		
Varistor voltage temperature coefficient	< 0.05	%/°C		
Capacitance measured at 1MHz	5	pF	Typical	
Capacitance tolerance	-50 to +50	%		
Insulation resistance after reflow soldering on PCB	> 10	ΜΩ		
Operating ambient temperature	-55 to +125	°C		
Storage temperature	-55 to +125	°C		



RELIABILITY TESTING PROCEDURES

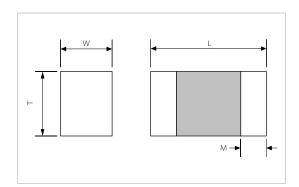
Reliability paraı	neter	Test methods and remarks	Test requirement
Pulse current capability	lmax 8/20 µs	IEC 1051-1, Test 4.5. 10 pulses in the same direction at 2 pulses per minute at maximum peak current	d Vn ∕Vn≤10% no visible damage
Electrostatic discharge capability	ESD C=150 pF, R=330Ω	IEC 1000-4-2 Each 10 times in positive/negative direction in 10 sec at 8KV contact discharge (Level 4)	d Vn /Vn≤10% no visible damage
	Thermal shock	IEC 68-2-14 Condition for 1 cycle Step 1 : Min. –40 °C , 30±3 min. Step 2 : Max. +125 °C , 30±3 min. Number of cycles: 30 times	d Vn /Vn≤5% no visible damage
	Low temperature	IEC 68-2-1 Place the chip at -40±5 °C for 1000±12hrs. Remove and place for 24±2hrs at room temp. condition, then measure	d Vn ∕Vn≤5% no visible damage
Environmenta	High temperature	IEC 68-2-2 Place the chip at 125±5 °C for 1000± 24hrs. Remove and place for 24±2hrs at room temp. condition, then measure	d Vn ∕Vn≤5% no visible damage
l reliability	Heat resistance	IEC 68-2-3 Apply the rated voltage for 1000±48hrs at 85±3 °C. Remove and place for 24±2hrs at room temp. condition, then measure	d Vn /Vn≤5% no visible damage
	Humidity resistance	IEC 68-2-30 Place the chip at 40±2°C and 90 to 95% humidity for 1000±24hrs. Remove and place for 24±2hrs at room temp. condition, then measure	d Vn ∕Vn≤10% no visible damage
	Pressure cooker test	Place the chip at 2 atm, 120°C, 85%RH for 60 hrs. Remove and place for 24±2hrs at room temp. condition, then measure	d Vn ∕Vn≤10% no visible damage
	Operating life	Apply the rated voltage for 1000±48hrs at 125±3 °C. Remove and place for 24±2hrs at room temp. condition, then measure	d Vn ∕Vn≤10% no visible damage
Mechanical Reliability	Adhesive strength	IEC 68-2-22 Applied force on SMD chip by fracture from PCB	Strength>10 N no visible damage



MATERIAL SPECIFICATION

Body	Internal electrode	External electrode	Thickness of Ni/Sn plating layer	
ZnO based ceramics	Silver – Palladium	Silver – Nickel – Tin	Nickel > 1 μm, Tin > 2 μm	

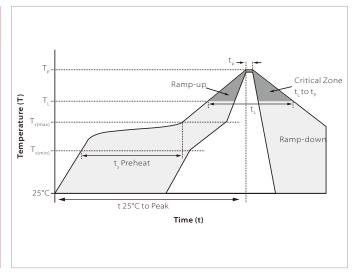
DIMENSION SPECIFICATION



Size	L(mm)	W(mm)	T(mm)	M(mm)
0402	1.0±0.10	0.5±0.10	≤ 0.6	0.20±0.10

SOLDERING RECOMMENDATIONS

Reflow Condition	Lead-free assembly
Temperature $Max(T_{s(min)})$	150°C
Temperature Max $(T_{s(max)})$	200°C
Time (min to max) (t_s)	60 – 180 secs
mp up rate (Liquidus Temp (T_L) to peak	3°C/second max
$T_{s_{(max)}}$ to T_{L} - Ramp-up Rate	3°C/second max
Temperature (T _L) (Liquidus)	217°C
Time (min to max) (t_L)	60 – 150 seconds
perature (T₅)	260°C
in 5°C of actual peak Temperature (t _p)	20 – 40 seconds
wn Rate	6°C/second max
C to peak Temperature (T٫)	8 minutes max.
cceed	260°C
	Temperature Max (T _{s(min)}) Temperature Max (T _{s(max)}) Time (min to max) (t _s) mp up rate (Liquidus Temp (T _L) to peak T _{s(max)} to T _L - Ramp-up Rate Temperature (T _L) (Liquidus) Time (min to max) (t _L) perature (T _p) in 5°C of actual peak Temperature (t _p) wn Rate To peak Temperature (T _p)





DRDERING INF ORMATIOON

Part Number	Package&Size	QTY/Reel	Reel Size
SME0402B5.0MA	0402 (1.0 x 0.5 mm)	10000PCS	7"



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